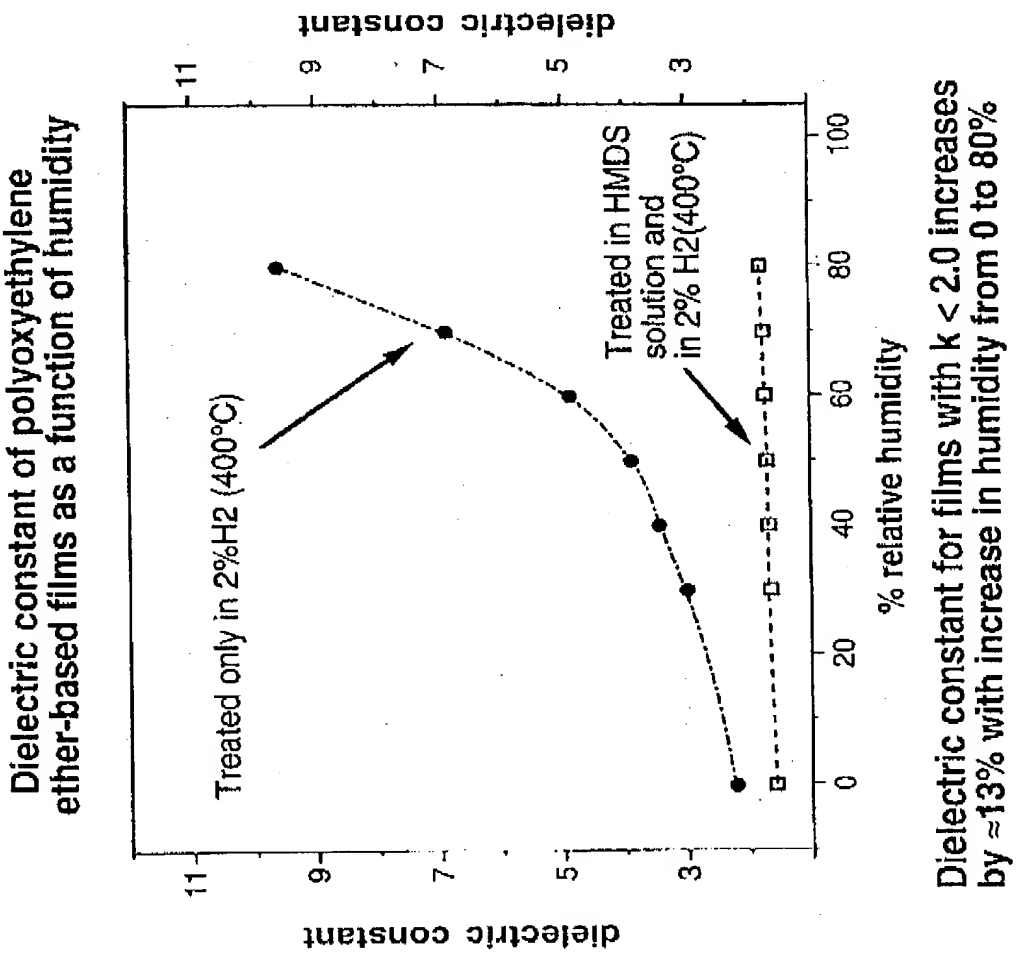
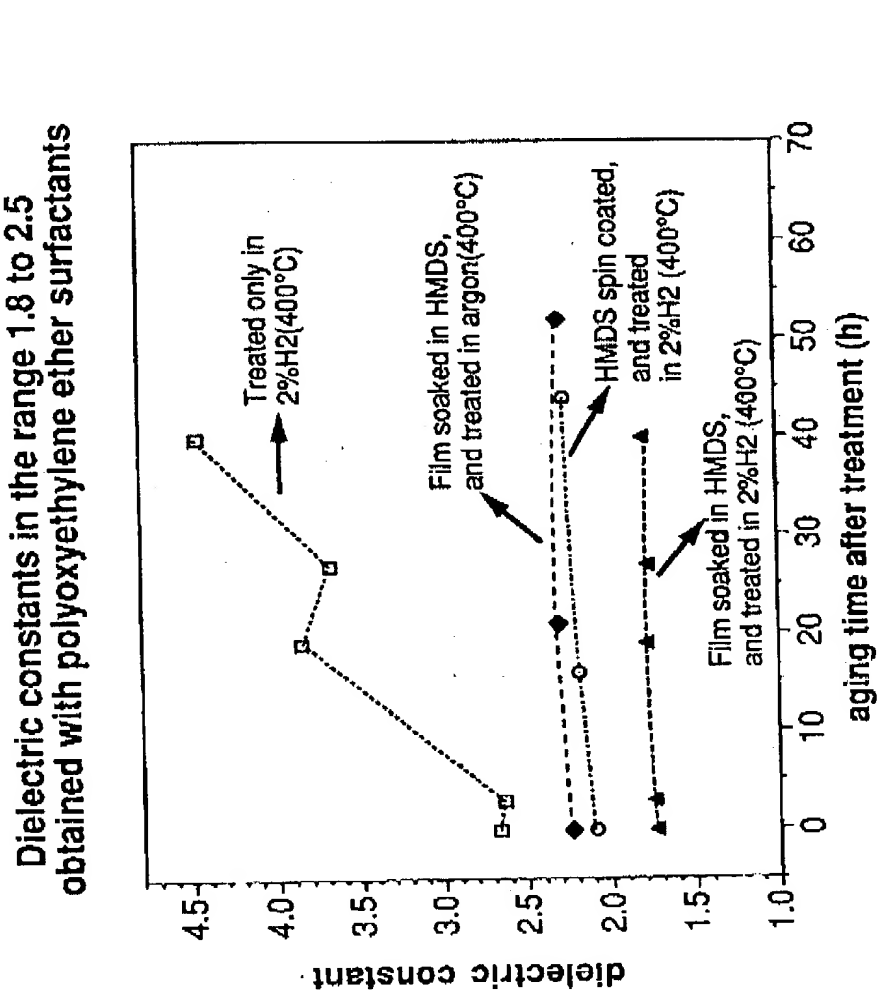
Exhibit A



Dielectric constant for films with k < 2.0 increases by ≈13% with increase in humidity from 0 to 80%

Exhibit B

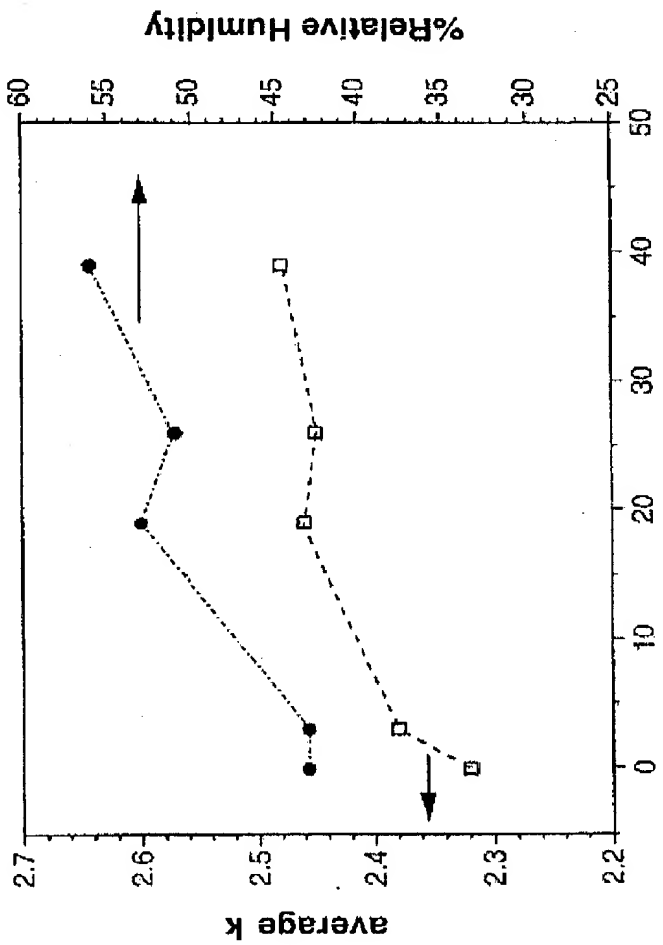


Dielectric constant very sensitive to dehydroxylation procedure

Exhibit C

CTAC pore former , with CTAC/TEOS mole ratio = 0.2

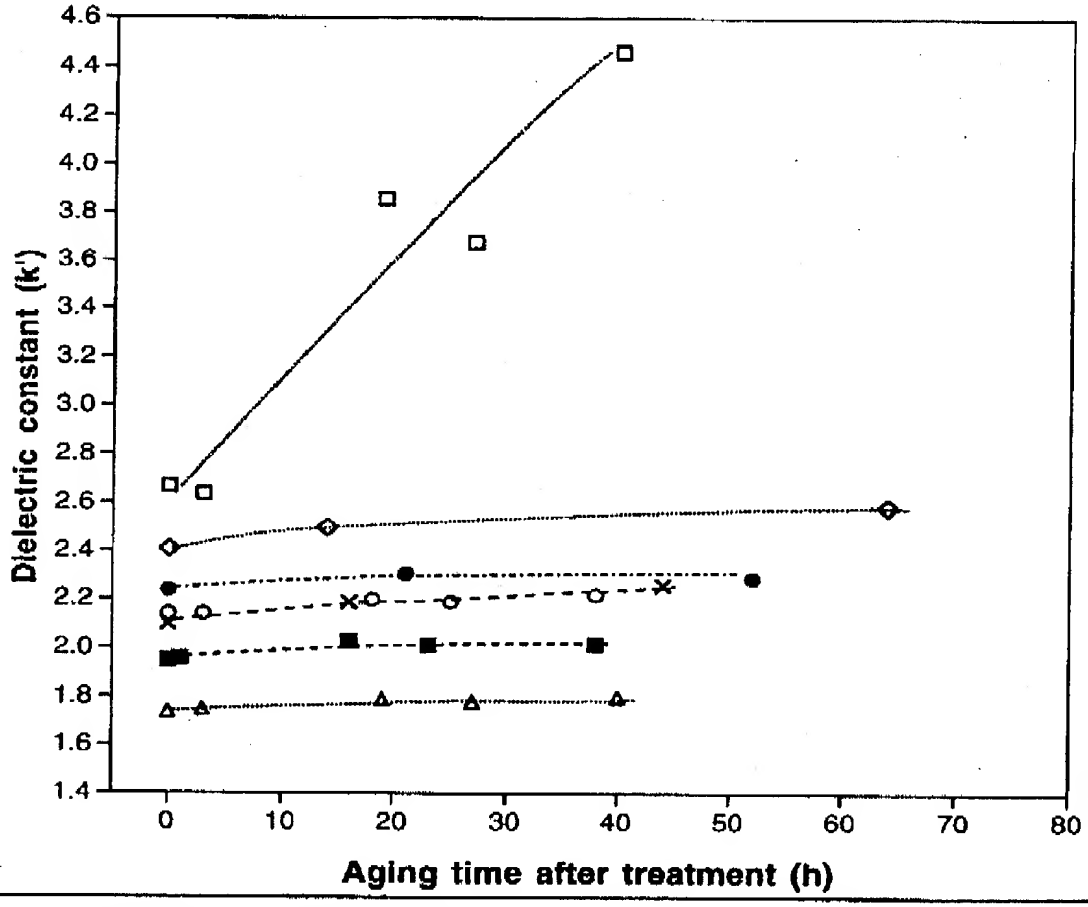
Acid-washed film treated in HMDS solution and 2%H2 (400°C, 3h)



k ≈ 2.3 measured in laboratory ambient

Exhibit D

Figure 1: Dielectric constant of surfactant-templated silica films as a function of aging time under ambient conditions as a function of various treatments



□	2%H2,2h,400°C (103-2-1-B1)
◇	HMDS (L)>>2%H2,2h,400°C (XL-92-2)
○	HMDS (L)>>2%H2, 2h,400°C>>HMDS(L) (103-2-I-A1)
△	HMDS (L)>>2%H2, 2h,400°C>>HMDS(L)>>2%H2,2h,400°C (103-2-I-A2)
■	HMDS (L)>> Ar,2h,400°C (103-2-1-B2)
●	HMDS(L)>>Ar,2h,400°C>>HMDS(L)>>Ar,2h,400 (112-1-III-D2)
×	HMDS spincoat>>2%H2,2h,400°C>>HMDS spin coat>>2%H2,2h,400°C (103-2-1-C1)

inventors - signatures with dates

witnesses - signatures with dates

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